

Si PIN photodiodes

S8385/S8729 series

SIP plastic package

The S8385/S8729 series is a family of large area Si PIN photodiodes molded into a miniature plastic SIP package (75% smaller in cubic volume than conventional types). Also available are lead forming types that save space when mounted on a PC board.

Features

- Small plastic package: 4 × 4.8 × 1.8 t mm
- 2-pin SIP lead type (lead length: 4.9 mm)
- High sensitivity, high-speed response
- **2** types of spectral response characteristics available S8385, S8729, S8729-10: for visible to infrared range (λ=320 to 1100 nm) S8729-04: for infrared (λ=760 to 1100 nm)
- Lead forming type also available (S8729-10)
- → Photosensitive area S8385: 2 × 2 mm

S8729 series: 2 × 3.3 mm

Applications

- **→** Barcode scanners
- **⇒** FSO
- Optical switches
- → Laser radar, etc.

Structure / Absolute maximum ratings

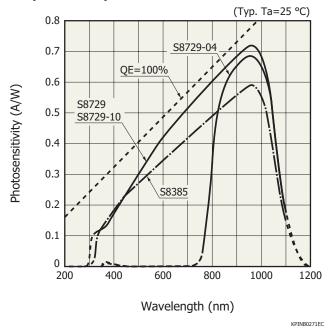
	Dimensional outline	Package	Photosensitive area size	Effective photosensitive area	Absolute maximum ratings				
Type no.					Reverse	Power	Operating	Storage	
					voltage	dissipation	temperature	temperature	
					VR max	Р	Topr	Tstg	
			(mm)	(mm²)	(V)	(mW)	(°C)	(°C)	
S8385			2 × 2	4					
S8729	1	Plastic			20	50	-25 to +85	-40 to +100	
S8729-04		ridSUC	2 × 3.3	6.6	20	50	-23 10 +83	-40 to +100	
S8729-10	2							I	

Note) Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

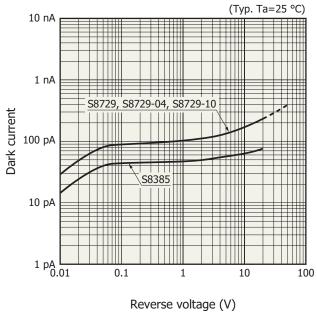
Electrical and optical characteristics

Type no.	Spectral response range λ	Peak sensitivity wavelength \(\lambda\)p		r -	(W)		Short circuit current Isc 100 lx	I VR=	current D =5 V	Temperature coefficient of ID TCID	$\lambda = 780 \text{ nm}$ RL=50 Ω	Terminal capacitance Ct VR=5 V f=1 MHz	NEP λ=λp
		, ,	λр	660	780	830		Тур.	Max.	((2.2)	-3 dB		0.44.1/2
	(nm)	(nm)	7.19	nm	nm	nm	(µA)	(nA)	(nA)	(times/°C)	(MHz)	(pF)	(W/Hz ^{1/2})
S8385	320 to 1100		0.56	0.4	0.48	0.5	4.2	0.1	1.0				1.0×10^{-14}
S8729	320 to 1100	960	0.7	0.45	0.55	0.6	7.5			1.15	25		1.1×10^{-14}
S8729-04	760 to 1100	300	0.68	-	-	0.52	5	0.2	2.0	1.15	23	16	1.2×10^{-14}
S8729-10	320 to 1100		0.7	0.45	0.55	0.6	7.5						1.1×10^{-14}

Spectral response

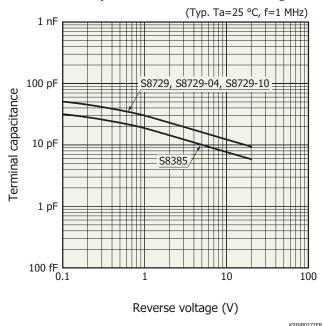


Dark current vs. reverse voltage



KPINB0273EB

Terminal capacitance vs. reverse voltage

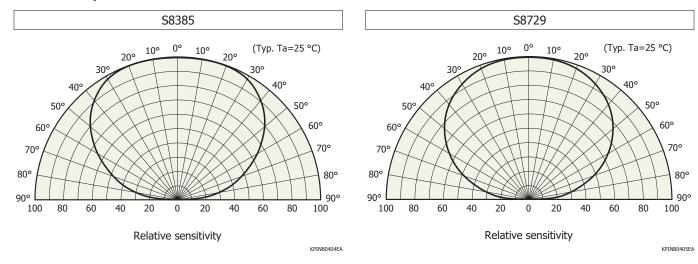


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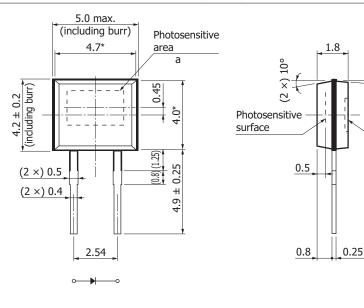
S8385/S8729 series

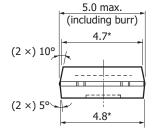
Directivity



- Dimensional outlines (unit: mm)

S8385, S8729, S8729-04





Symbol	S8385	S8729 S8729-04			
а	2 × 2	2 × 3.3			

Tolerance unless otherwise noted: ± 0.1 , $\pm 2^{\circ}$ Chip position accuracy with respect to the package dimensions marked * X, Y $\leq \pm 0.2$, $\theta \leq \pm 2^{\circ}$

φ2.0

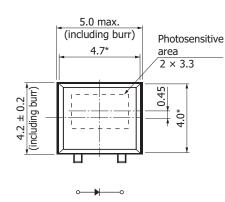
Depth 0.15 max.

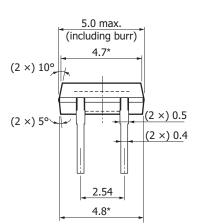
Standard packing: stick (50 pcs/stick)

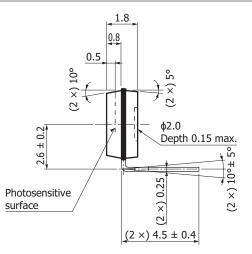
KPINA0090EC



S8729-10







Tolerance unless otherwise noted: ±0.1, ±2° Chip position accuracy with respect to the package dimensions marked * X, Y≤±0.2, θ≤±2°

Standard packing: stick (50 pcs/stick)

KPINA0091EC

Related information

www.hamamatsu.com/sp/ssd/doc_en.html

- Precautions
 - Disclaimer
 - · Metal, ceramic, plastic package products
- Technical information
 - · Si photodiode/Application circuit examples

Information described in this material is current as of April 2019.

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